

BUK9Y43-60E

N-channel 60 V, 43 mΩ logic level MOSFET in LFPAK56 Product data sheet

1. **General description**

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. **Features and benefits**

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

Applications 3.

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	22	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	45	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	35.8	43	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; V_{DS} = 48 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	3.4	-	nC



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	[q]	G
4	G	gate	و ق ق ق	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9Y43-60E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y43-60E	94360E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

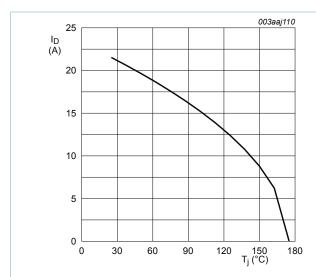
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	60	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		T _j ≤ 175 °C; Pulsed	[1][2]	-15	15	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	22	Α
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 1</u>		-	15	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4		-	86	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	45	W

BUK9Y43-60E

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Symbol	Parameter	Conditions		Min	Max	Unit	
T _{stg}	storage temperature			-55	175	°C	
Tj	junction temperature			-55	175	°C	
Source-drain	Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	22	Α	
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	86	Α	
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 22 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[3][4]	-	12.4	mJ	

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_j$ and or $\rm V_{GS}$
- [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information.



Continuous drain current as a function of Fig. 1. mounting base temperature

$$V_{GS} \ge 5V$$

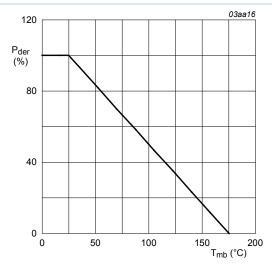


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \,\%$$

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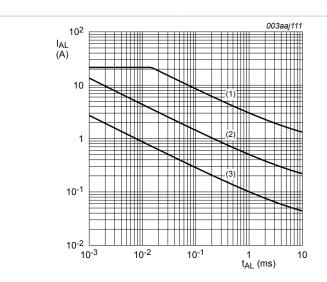
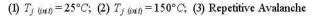


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



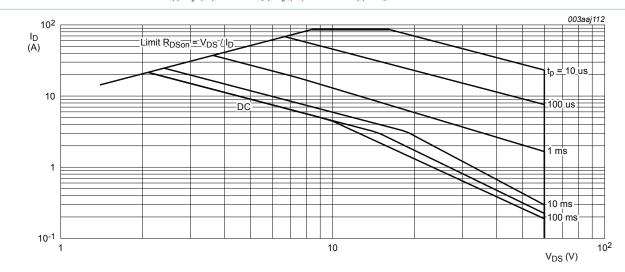


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

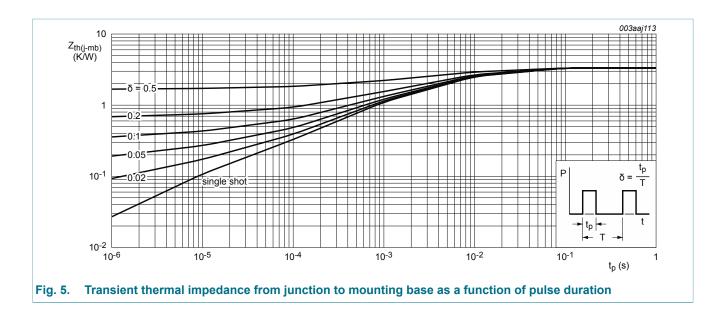
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	_	3.33	K/W

BUK9Y43-60E

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N-channel 60 V, 43 m Ω logic level MOSFET in LFPAK56



10. Characteristics

Table 7. **Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						_
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		60	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C		54	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10		1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9		-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9		0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C		-	0.01	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C		-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>		-	35.8	43	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>		-	31	38	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 12; Fig. 11		-	-	97.2	mΩ
Dynamic ch	naracteristics		'		'	'	
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 48 V; V _{GS} = 5 V;		-	8.2	-	nC
Q_{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>		-	1.6	-	nC
Q _{GD}	gate-drain charge			-	3.4	-	nC
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Product data sheet 8 May 2013 5/13

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	660	880	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	90	110	pF
C _{rss}	reverse transfer capacitance			-	60	85	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 45 \text{ V}; R_{L} = 5 \Omega; V_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_{j} = 25 \text{ °C}$		-	6.3	-	ns
t _r	rise time			-	12.3	-	ns
$t_{d(off)}$	turn-off delay time			-	10.1	-	ns
t _f	fall time			-	10.6	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.83	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}; \text{ T}_j = 25 \text{ °C}$		-	17.5	-	ns
Q _r	recovered charge			-	11.2	-	nC

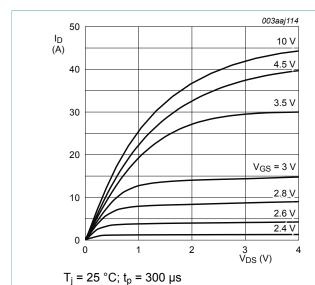


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

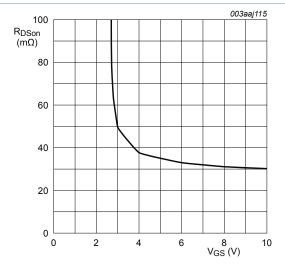


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; \ I_D = 5A$$

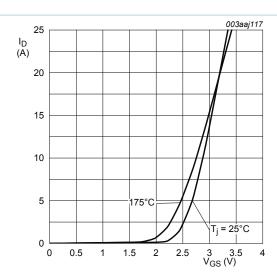


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



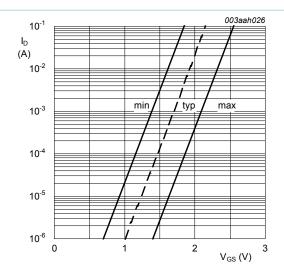


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C; $V_{DS} = 5V$

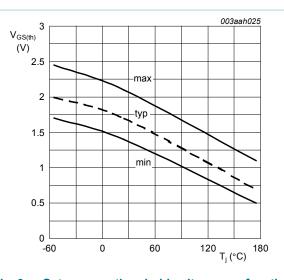
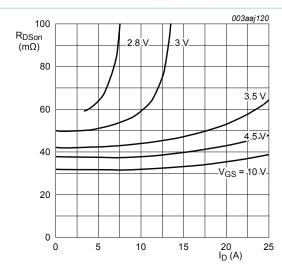


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$



 $T_i = 25 \, ^{\circ}C; t_p = 300 \, \mu s$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

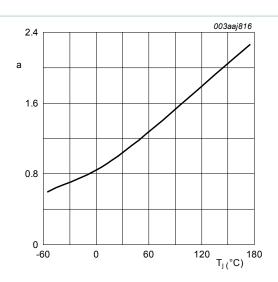


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

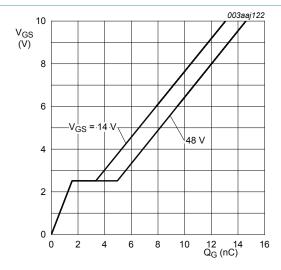


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 5A$

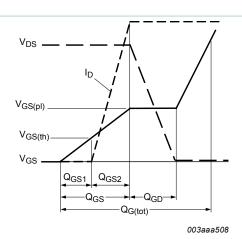


Fig. 13. Gate charge waveform definitions

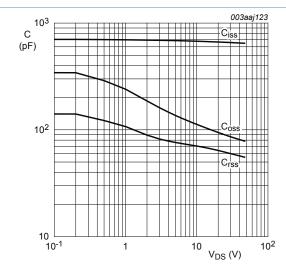


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

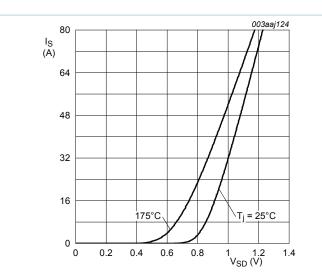


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

N-channel 60 V, 43 mΩ logic level MOSFET in LFPAK56

11. Package outline

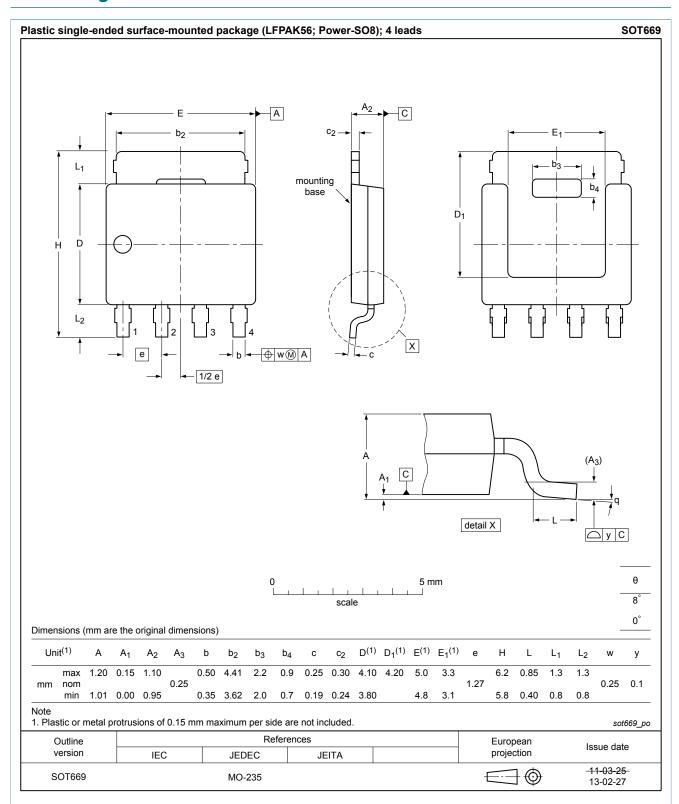


Fig. 17. Package outline LFPAK56; Power-SO8 (SOT669)

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N-channel 60 V, 43 m Ω logic level MOSFET in LFPAK56

13. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	5
11	Package outline	10
12	Legal information	11
12.1	Data sheet status	11
12.2	Definitions	11
12.3	Disclaimers	11
12.4	Trademarks	12

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